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Author index

Aarik, J., A. Aidla, H. Mändar, V. Sammelselg and T. Uustare, Texture development in nanocrystalline hafnium dioxide thin films grown by atomic layer deposition 220 (2000) 105

Aarik, J., A. Aidla, H. Mändar and V. Sammelselg, Anomalous effect of temperature on atomic layer deposition of titanium dioxide 220 (2000) 531

Abe, S. and K. Masumoto, Compositional plane of a new quaternary solid solution semiconductor $Pb_{1-x}(Mg_{1-y}Sr_y)_xS$ for mid-infrared lasers 220 (2000) 126

Adachi, G., see Imanaka, N. 220 (2000) 176

Aguilera Morales, S., see Falcón Rodríguez, C. 220 (2000) 130

Aidla, A., see Aarik, J. 220 (2000) 105

Aidla, A., see Aarik, J. 220 (2000) 531

Amano, C., see Tateno, K. 220 (2000) 393

Ambacher, O., see Lima, A.P. 220 (2000) 341

Arai, K., see Nasir Khan, M. 220 (2000) 75

Asghar, M., see Krispin, P. 220 (2000) 220

Assmus, W., see Prokofiev, A.V. 220 (2000) 345

Baç, N., see Warzywoda, J. 220 (2000) 140

Baç, N., see Warzywoda, J. 220 (2000) 150

Bacchin, G., see Umeno, A. 220 (2000) 355

Backofen, R., see Metzger, M. 220 (2000) 6

Bahng, W., see Nasir Khan, M. 220 (2000) 75

Bao, C.L., see Zhang, Y.H. 220 (2000) 351

Bar-Yoseph, P.Z., see Gelfgat, A.Yu. 220 (2000) 316

Barz, R.-U., see Grassl, M. 220 (2000) 522

Belas, E., see Höschl, P. 220 (2000) 444

Bello, I., see Lam, C. 220 (2000) 466

Bennett, B.R., see Bracker, A.S. 220 (2000) 384

Blanks, K.A., Novel synthesis of gibbsite by laser-stimulated nucleation in supersaturated sodium aluminate solutions 220 (2000) 572

Bo Shim, K., see Jung, I.H. 220 (2000) 275

Boisvert, J.-P., M. Domenech, A. Foissy, J. Persello and J.-C. Mutin, Hydration of calcium sulfate hemihydrate ($CaSO_4 \cdot \frac{1}{2}H_2O$) into gypsum ($CaSO_4 \cdot 2H_2O$). The influence of the sodium poly(acrylate)/surface interaction and molecular weight 220 (2000) 579

Boudet, N., see Smilgies, D.-M. 220 (2000) 88

Bove, P., D.J. Rogers and F. Hosseini Teherani, Atomic layer-by-layer growth of superconducting Bi–Sr–Ca–Cu–O thin films by molecular beam epitaxy 220 (2000) 68

Bracker, A.S., M.J. Yang, B.R. Bennett, J.C. Culbertson and W.J. Moore, Surface reconstruction phase diagrams for InAs, AlSb, and GaSb 220 (2000) 384

Brinkman, A.W., see Halliday, D.P. 220 (2000) 30

Chahoud, M., D. Fehly, H.-H. Wehmann and A. Schlachetzki, Cellular-automata-based simulation of anisotropic crystal growth 220 (2000) 471

Chai, B.H.T., see Nicholls, J.F.H. 220 (2000) 263

Chang, S.J., see Subba Ramaiah, K. 220 (2000) 405

Chen, C.H., see Subba Ramaiah, K. 220 (2000) 405

Chen, H., see Wan, L. 220 (2000) 379

Chen, H.B., see Liu, J.F. 220 (2000) 488

Chen, M., Z.L. Pei, C. Sun, L.S. Wen and X. Wang, Surface characterization of transparent conductive oxide Al-doped ZnO films 220 (2000) 254

Chen, W., see Liang, C.H. 220 (2000) 296

Cheng, J.G., see Meng, X.J. 220 (2000) 100

Cheng, Ruiping, see Wang, Changqing 220 (2000) 114

Cho, A.Y., see Ng, H.M. 220 (2000) 432

Cho, H.K., J.Y. Lee, K.S. Kim and G.M. Yang, Phase separation and stacking fault of $In_xGa_{1-x}N$ layers grown on thick GaN and sapphire substrate by metalorganic chemical vapor deposition 220 (2000) 197

Cho, M.-H., D.-H. Ko, Y.G. Choi, I.W. Lyo, K. Jeong and C.N. Whang, Effects of SiO_2 overlayer at initial growth stage of epitaxial Y_2O_3 film growth 220 (2000) 501

Choi, C.K., see Hwang, I.G. 220 (2000) 326

Choi, I.-H., see Hwang, S.-M. 220 (2000) 56

Choi, W.-B., see Park, G.-S. 220 (2000) 494

0022-0248/00/$ - see front matter © 2000 Elsevier Science B.V. All rights reserved.
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Choi, Y.C., see Park, G.-S. 220 (2000) 494
Choi, Y.G., see Cho, M.-H. 220 (2000) 501
Chow, Y.T., see Wang, Changqing 220 (2000) 114
Chu, J.H., see Meng, X.J. 220 (2000) 100
Chu, S.N.G., see Ng, H.M. 220 (2000) 432
Cohen, R.M., see Reichert, W. 220 (2000) 364
Culbertson, J.C., see Bracker, A.S. 220 (2000) 384

Dabkowska, H., see Imanaka, N. 220 (2000) 176
Dabkowski, A., see Imanaka, N. 220 (2000) 176
De Graef, M., see Ha, S. 220 (2000) 308
Ding, D., see Liu, H.Y. 220 (2000) 216
Ding, D., see Liu, F.-Q. 220 (2000) 439
Doki, N., see Kubota, N. 220 (2000) 135
Domenech, M., see Boisvert, J.-P. 220 (2000) 579
Duan, X.F., see Wan, L. 220 (2000) 379
Dubois, C., see Koumetz, S. 220 (2000) 46

Edgar, J.H., see Liu, L. 220 (2000) 243

Falcón Rodríguez, C., F. Falcón Rodríguez, S. Aguilera Morales and R. Mulet Genicio, Crystallization simulation in macromolecular crystals 220 (2000) 130
Falcón Rodríguez, F., see Falcón Rodríguez, C. 220 (2000) 130
Fan, X.W., see Yang, Y. 220 (2000) 286
Fehly, D., see Chahoud, M. 220 (2000) 471
Feng, J.Y., see Liu, J.F. 220 (2000) 488
Feng, S.L., see Wang, X.D. 220 (2000) 16
Fesh, R., see Höschl, P. 220 (2000) 444
Foissy, A., see Boisvert, J.-P. 220 (2000) 579
Franc, J., see Höschl, P. 220 (2000) 444
Fu, X., J. Li, Z. Song and C. Lin, Growth of highly (1 0 0)-oriented Zr-rich PZT thin films on Pt/Ti/SiO_2/Si substrates by a simple sol–gel process 220 (2000) 82
Fujita, K., see Shibata, M. 220 (2000) 449
Fukuda, T., see Jung, I.H. 220 (2000) 275
Fukuda, T., see Tomm, Y. 220 (2000) 510
Furukawa, Y. and S. Noda, Difference of anisotropic structures of InAs/GaAs quantum dots between organometallic vapor-phase epitaxy and molecular beam epitaxy 220 (2000) 425

Gallagher, H.G., see Nicholls, J.F.H. 220 (2000) 263
Gao, F., D.D. Huang, J.P. Li, Y.X. Lin, M.Y. Kong, J.M. Li, Y.P. Zeng and L.Y. Lin, The growth of Si/SiGe/Si structures for heterojunction bipolar transistor by gas source molecular beam epitaxy 220 (2000) 457
Gao, F., D.D. Huang, J.P. Li, Y.X. Lin, M.Y. Kong, D.Z. Sun, J.M. Li and L.Y. Lin, Influence of phosphine flow rate on Si growth rate in gas source molecular beam epitaxy 220 (2000) 461
Garandet, J.P., see Haddad, F.Z. 220 (2000) 166
Gelfgat, A.Yu., P.Z. Bar-Yoseph and A. Solan, Axisymmetry breaking instabilities of natural convection in a vertical bridgman growth configuration 220 (2000) 316
Gheorghe, L., M. Petrache and V. Lupei, Preparation, growth, and characterisation of Nd^{3+}-doped calcium lithium niobium gallium garnet (Nd^{3+}:CLNGG) single crystals 220 (2000) 121
Gille, P., see Grassl, M. 220 (2000) 522
Gmachl, C., see Ng, H.M. 220 (2000) 432
Gong, Q., R. Nötzel, H.-P. Schönherr and K.H. Ploog, Study of molecular-beam epitaxy growth on patterned GaAs (3 1 1)A substrates with different mesa height 220 (2000) 23
Gorochov, O., see Sallet, V. 220 (2000) 209
Grassl, M., R.-U. Barz and P. Gille, Etch studies on $GaPO_4$ single crystals 220 (2000) 522
Grill, R., see Höschl, P. 220 (2000) 444
Gu, C.-Y., see Ji, W. 220 (2000) 560
Guo, S.L., see Meng, X.J. 220 (2000) 100

Ha, S., N.T. Nuhfer, G.S. Rohrer, M. De Graef and M. Skowronski, Origin of domain structure in hexagonal silicon carbide boules grown by the physical vapor transport method 220 (2000) 308
Haddad, F.Z., J.P. Garandet, D. Henry and H.Be Hadid, Analysis of the unsteady segregation in crystal growth from a melt Part II: Fluctuating convection velocity 220 (2000) 166
Hadid, H.Be, see Haddad, F.Z. 220 (2000) 166
Halliday, D.P., M.D.G. Potter, J.T. Mullins and A.W. Brinkman, Photoluminescence study of a bulk vapour grown CdTe crystal 220 (2000) 30
Hallin, C., see Ji, W. 220 (2000) 560
Haut, C., see Velázquez, M. 220 (2000) 480
He, L., see Wang, S. 220 (2000) 548
Henderson, B., see Nicholls, J.F.H. 220 (2000) 263
Hennion, B., see Velázquez, M. 220 (2000) 480
Henry, D., see Haddad, F.Z. 220 (2000) 166
Hiiro, S., see Ohshita, Y. 220 (2000) 604
Hirai, S., see Tabe, Y. 220 (2000) 180
Hiraiwa, M., see Imanaka, N. 220 (2000) 176
Hiroyama, Y., see Wang, D. 220 (2000) 204
Ho Auh, K., see Jung, I.H. 220 (2000) 275
Horng, R.-H., see Wuu, D.-S. 220 (2000) 235
Hoshino, A., see Ohshita, Y. 220 (2000) 604
Hosseini Teherani, F., see Bove, P. 220 (2000) 68
Höschl, P., E. Belas, L. Turjanska, R. Grill, J. Franc, R. Fesh and P. Moravec, High-temperature conductivity of solid and liquid CdTe 220 (2000) 444
Huang, D.D., see Gao, F. 220 (2000) 457

Huang, D.D., see Gao, F. 220 (2000) 461
Huang, Q., see Zhang, Y.H. 220 (2000) 351
Huang, Q., see Wan, L. 220 (2000) 379
Hwang, I.G. and C.K. Choi, The onset of mushy-layer-mode instabilities during solidification in ammonium chloride solution 220 (2000) 326
Hwang, S.-M., Y. Ju Park, J. Nah, E. Kyu Kim and I.-H. Choi, Growth behavior of GaAs/AlGaAs multi-layers grown on U-grooved GaAs fusion layer on InP substrate 220 (2000) 56

Ichikawa, M., see Wang, D. 220 (2000) 204
Ichikawa, M., see Shibata, M. 220 (2000) 449
Ihaddadene, M., see Koumetz, S. 220 (2000) 46
Imanaka, N., M. Hiraiwa, G. Adachi, H. Dabkowska and A. Dabkowski, Thermal contraction behavior in $Al_2(WO_4)_3$ single crystal 220 (2000) 176
Ito, T., see Kangawa, Y. 220 (2000) 401

Jansen, J.C., see Warzywoda, J. 220 (2000) 140
Jeong, K., see Cho, M.-H. 220 (2000) 501
Ji, R., see Wang, S. 220 (2000) 548
Ji, W., P.M. Lofgren, C. Hallin, C.-Y. Gu and G. Zhou, Computational modeling of SiC epitaxial growth in a hot wall reactor 220 (2000) 560
Jiang, D.-S., see Liu, F.-Q. 220 (2000) 439
Joesten, R., see Warzywoda, J. 220 (2000) 150
Joubert, E., see Koumetz, S. 220 (2000) 46
Ju Park, Y., see Hwang, S.-M. 220 (2000) 56
Juang, F.S., see Subba Ramaiah, K. 220 (2000) 405
Jung, I.H.,, J. Min Ko, K. Bo Shim, T. Fukuda and K. Ho Auh, Influence of starting melt composition on $La_3(Ta_xGa_{1-x})\ Ga_5O_{14}$ crystals grown by Czochralski method 220 (2000) 275

Kangawa, Y., T. Ito, A. Mori and A. Koukitu, Anomalous behavior of excess energy curves of $In_xGa_{1-x}N$ grown on GaN and InN 220 (2000) 401
Karrer, U., see Lima, A.P. 220 (2000) 341
Kawabata, K., see Maruyama, M. 220 (2000) 161
Kean, A., see Najda, S.P. 220 (2000) 226
Ketata, K., see Koumetz, S. 220 (2000) 46
Ketata, M., see Koumetz, S. 220 (2000) 46
Kim, J.-M., see Park, G.-S. 220 (2000) 494
Kim, K.S., see Cho, H.K. 220 (2000) 197
Kiselev, N.A., see Roddatis, V.V. 220 (2000) 515
Klimm, D., see Tomm, Y. 220 (2000) 510
Knauer, A., see Krispin, P. 220 (2000) 220
Ko, D.-H., see Cho, M.-H. 220 (2000) 501
Kong, M.Y., see Gao, F. 220 (2000) 457
Kong, M.Y., see Gao, F. 220 (2000) 461
Kostial, H., see Krispin, P. 220 (2000) 220
Koukitu, A., see Kangawa, Y. 220 (2000) 401
Koumetz, S., K. Ketata, M. Ihaddadene, E. Joubert, M. Ketata and C. Dubois, Be diffusion in InGaAs/InP heterostructures grown by gas source molecular beam epitaxy 220 (2000) 46
Kozhemyakin, G.N., Indium inhomogeneity in $In_xGa_{1-x}Sb$ ternary crystals grown by floating crucible Czochralski method 220 (2000) 39
Krispin, P., M. Asghar, A. Knauer and H. Kostial, Interface properties of isotype GaAs/(In,Ga)P/GaAs heterojunctions grown by metalorganic-vapour-phase epitaxy on GaAs 220 (2000) 220
Kubota, N., H. Otosaka, N. Doki, M. Yokota and A. Sato, Effect of lead(II) impurity on the growth of sodium chloride crystals 220 (2000) 135
Kulinich, S.A., see Majima, T. 220 (2000) 336
Kung, C.-Y., see Wuu, D.-S. 220 (2000) 235
Kuribayashi, N., see Maruyama, M. 220 (2000) 161
Kyu Kim, E., see Hwang, S.-M. 220 (2000) 56

Lam, C., Y.F. Zhang, Y.H. Tang, C.S. Lee, I. Bello and S.T. Lee, Large-scale synthesis of ultrafine Si nanoparticles by ball milling 220 (2000) 466
Lan, C.W. and C.Y. Tu, Morphological instability due to double diffusive convection in directional solidification: the pit formation 220 (2000) 619
Lee, C.-R., Electronic characteristics of $Au/Al_xGa_{1-x}N$ structures grown with various x values 220 (2000) 62
Lee, C.S., see Lam, C. 220 (2000) 466
Lee, J.Y., see Cho, H.K. 220 (2000) 197
Lee, S.T., see Lam, C. 220 (2000) 466
Lee, Y.H., see Park, G.-S. 220 (2000) 494
Li, A., see Li, Aidong 220 (2000) 291
Li, Aidong, C. Xu, A. Li and N. Ming, Study of coloration, microbe inhibition during the growth of L-arginine phosphate monohydrate single crystals 220 (2000) 291
Li, G., see Wang, S. 220 (2000) 548
Li, J., see Fu, X. 220 (2000) 82
Li, J.M., see Gao, F. 220 (2000) 457
Li, J.M., see Gao, F. 220 (2000) 461
Li, J.P., see Gao, F. 220 (2000) 457
Li, J.P., see Gao, F. 220 (2000) 461
Li, N., R.A. Shanks and D.M. Murphy, Microscopic study of polymorphism of a photographic coupler 220 (2000) 592
Li, S.D., see Zhan, J.H. 220 (2000) 231
Li, Z., see Wan, L. 220 (2000) 379
Liang, C.H., G.W. Meng, W. Chen, Y.W. Wang and L.D. Zhang, Growth and characterization of TiC nanorods activated by nickel nanoparticles 220 (2000) 296

Lim, C.-B., see Park, G.-S. 220 (2000) 494
Lima, A.P., C.R. Miskys, U. Karrer, O. Ambacher, A. Wenzel, B. Rauschenbach and M. Stutzmann, Growth of quaternary AlInGaN/GaN heterostructures by plasma-induced molecular beam epitaxy 220 (2000) 341
Lin, C., see Fu, X. 220 (2000) 82
Lin, L.Y., see Gao, F. 220 (2000) 457
Lin, L.Y., see Gao, F. 220 (2000) 461
Lin, W.-T., see Wuu, D.-S. 220 (2000) 235
Lin, Y.X., see Gao, F. 220 (2000) 457
Lin, Y.X., see Gao, F. 220 (2000) 461
Liu, B.L., Z.Y. Xu, H.Y. Liu and Z.G. Wang, Strong temperature dependence of photoluminescence properties in visible InAlAs quantum dots 220 (2000) 51
Liu, F.-Q., D. Ding, B. Xu, Y.-Z. Zhang, Q.-S. Zhang, Z.-G. Wang, D.-S. Jiang and B.-Q. Sun, Strain-compensated quantum cascade lasers operating at room temperature 220 (2000) 439
Liu, H., see Yin, J. 220 (2000) 281
Liu, H., see Wan, L. 220 (2000) 379
Liu, H.Y., see Liu, B.L. 220 (2000) 51
Liu, H.Y., X.D. Wang, Y.Q. Wei, B. Xu, D. Ding and Z.G. Wang, Effects of interdiffusion on the luminescence of InAs/GaAs quantum dots covered by InGaAs overgrowth layer 220 (2000) 216
Liu, J.F., H.B. Chen and J.Y. Feng, Enhanced thermal stability of NiSi films on Si(1 1 1) substrates by a thin Pt interlayer 220 (2000) 488
Liu, J.M., see Yin, J. 220 (2000) 281
Liu, L. and J.H. Edgar, Transport effects in the sublimation growth of aluminum nitride 220 (2000) 243
Liu, Xuesong, see Wang, Changqing 220 (2000) 114
Liu, Y.N., see Yang, Y. 220 (2000) 286
Liu, Z.G., see Yin, J. 220 (2000) 281
Lofgren, P.M., see Ji, W. 220 (2000) 560
Lu, L.W., see Zhang, Y.H. 220 (2000) 351
Lupei, V., see Gheorghe, L. 220 (2000) 121
Lusson, A., see Sallet, V. 220 (2000) 209
Lyo, I.W., see Cho, M.-H. 220 (2000) 501

Machida, H., see Ohshita, Y. 220 (2000) 604
Majima, T., H. Yamamoto, S.A. Kulinich and K. Terashima, High-rate deposition of $LiNb_{1-x}Ta_xO_3$ films by thermal plasma spray CVD 220 (2000) 336
Marin, C., see Nicoara, I. 220 (2000) 1
Maruyama, M., K. Kawabata and N. Kuribayashi, Crystal morphologies and melting curves of CCl_4 at pressures up to 330 MPa 220 (2000) 161
Masumoto, K., see Abe, S. 220 (2000) 126
Meng, G.W., see Liang, C.H. 220 (2000) 296
Meng, X.J., J.G. Cheng, J.L. Sun, H.J. Ye, S.L. Guo and J.H. Chu, Growth of (1 0 0)-oriented $LaNiO_3$ thin films directly on Si substrates by a simple metalorganic decomposition technique for the highly oriented PZT thin films 220 (2000) 100
Meng, Xianlin, see Wang, Changqing 220 (2000) 114
Metzger, M. and R. Backofen, Optimal temperature profiles for annealing of GaAs-crystals 220 (2000) 6
Miao, Z.H., see Wang, X.D. 220 (2000) 16
Miki, O., see Tsuchiya, T. 220 (2000) 185
Min Ko, J., see Jung, I.H. 220 (2000) 275
Ming, N., see Li, Aidong 220 (2000) 291
Miskys, C.R., see Lima, A.P. 220 (2000) 341
Mändar, H., see Aarik, J. 220 (2000) 105
Mändar, H., see Aarik, J. 220 (2000) 531
Moore, W.J., see Bracker, A.S. 220 (2000) 384
Moravec, P., see Höschl, P. 220 (2000) 444
Mori, A., see Kangawa, Y. 220 (2000) 401
Mulet Genicio, R., see Falcón Rodríguez, C. 220 (2000) 130
Mullins, J.T., see Halliday, D.P. 220 (2000) 30
Murphy, D.M., see Li, N. 220 (2000) 592
Mutin, J.-C., see Boisvert, J.-P. 220 (2000) 579

Nah, J., see Hwang, S.-M. 220 (2000) 56
Najda, S.P., A. Kean, R.W. Streater and A.J. SpringThorpe, SIMS measurements of oxygen impurities in AlGaInP semiconductor material and laser diodes 220 (2000) 226
Nakajima, K., T. Ujihara, G. Sazaki and Noritaka Usami, Phase diagram calculation for epitaxial growth of GaInAs on InP considering the surface, interfacial and strain energies 220 (2000) 413
Nasir Khan, M., S.-i. Nishizawa, W. Bahng and K. Arai, Liquid-phase epitaxy on 6H-SiC Acheson seed crystals in closed vessel 220 (2000) 75
Ng, H.M., C. Gmachl, S.N.G. Chu and A.Y. Cho, Molecular beam epitaxy of $GaN/Al_xGa_{1-x}N$ superlattices for 1.52–4.2 μm intersubband transitions 220 (2000) 432
Nicholls, J.F.H., B. Henderson, H.G. Gallagher and B.H.T. Chai, Synthesis, growth and assessment of mixed niobate–borate (XYB_2O_6) compounds 220 (2000) 263
Nicoara, D., see Nicoara, I. 220 (2000) 1
Nicoara, I., D. Nicoara, A.G. Ostrogorsky, C. Marin and T. Peignier, Growth and characterization of shaped GaSb crystals 220 (2000) 1
Nishinaga, T., see Umeno, A. 220 (2000) 355
Nishizawa, S.-i., see Nasir Khan, M. 220 (2000) 75
Nitta, Y., see Shibata, M. 220 (2000) 449
Niu, Z.C., see Wang, X.D. 220 (2000) 16
Noda, S., see Furukawa, Y. 220 (2000) 425
Noritaka Usami, see Nakajima, K. 220 (2000) 413

Nötzel, R., see Gong, Q. 220 (2000) 23
Nuhfer, N.T., see Ha, S. 220 (2000) 308

Ogura, A., see Ohshita, Y. 220 (2000) 604
Ohnishi, M., see Tsuchiya, T. 220 (2000) 185
Ohnishi, M., see Tsuchiya, T. 220 (2000) 191
Ohshita, Y., A. Ogura, A. Hoshino, S. Hiiro and H. Machida, Low-pressure chemical vapor deposition of TaCN films by pyrolysis of ethylamido-tantalum 220 (2000) 604
Okazaki, K., see Tabe, Y. 220 (2000) 180
Ong, P.P., see Wang, H. 220 (2000) 554
Ostrogorsky, A.G., see Nicoara, I. 220 (2000) 1
Otosaka, H., see Kubota, N. 220 (2000) 135

Pandey, P., see Rai, U.S. 220 (2000) 610
Pang, Q., see Wang, S. 220 (2000) 548
Park, G.-S., W.-B. Choi, J.-M. Kim, Y.C. Choi, Y.H. Lee and C.-B. Lim, Structural investigation of gallium oxide (β-Ga_2O_3) nanowires grown by arc-discharge 220 (2000) 494
Pei, Z.L., see Chen, M. 220 (2000) 254
Peignier, T., see Nicoara, I. 220 (2000) 1
Persello, J., see Boisvert, J.-P. 220 (2000) 579
Petrache, M., see Gheorghe, L. 220 (2000) 121
Pimpinelli, A., see Vladimirova, M. 220 (2000) 631
Ploog, K.H., see Gong, Q. 220 (2000) 23
Potter, M.D.G., see Halliday, D.P. 220 (2000) 30
Prokofiev, A.V., D. Wichert and W. Assmus, Crystal growth of the quasi-one dimensional spin-magnet $LiCuVO_4$ 220 (2000) 345

Qian, Y.T., see Zhan, J.H. 220 (2000) 231

Rai, R.N., see Rai, U.S. 220 (2000) 610
Rai, U.S., P. Pandey and R.N. Rai, Physical chemistry of binary organic eutectic and monotectic alloys; 1,2,4,5-tetrachlorobenzene–β-naphthol and 1,2,4,5-tetramethylbenzene-succinonitrile systems 220 (2000) 610
Rauschenbach, B., see Lima, A.P. 220 (2000) 341
Reiche, P., see Tomm, Y. 220 (2000) 510
Reichert, W. and R.M. Cohen, Lateral OMVPE growth of GaAs on patterned substrates 220 (2000) 364
Revcolevschi, A., see Velázquez, M. 220 (2000) 480
Roddatis, V.V., E.A. Stepantsov and N.A. Kiselev, HREM investigations of intermediate ZnO and ZnO/Y–ZrO_2 layers in Y–ZrO_2 bicrystals and ZnO films grown on Y–ZrO_2 bicrystal substrates 220 (2000) 515
Rogers, D.J., see Bove, P. 220 (2000) 68
Rohrer, G.S., see Ha, S. 220 (2000) 308
Rommeluere, M., see Sallet, V. 220 (2000) 209
Rossetti Jr., G.A., see Warzywoda, J. 220 (2000) 150
Roux, B., see Tatarchenko, V.A. 220 (2000) 301

Sacco Jr., A., see Warzywoda, J. 220 (2000) 140
Sacco Jr., A., see Warzywoda, J. 220 (2000) 150
Sallet, V., A. Lusson, M. Rommeluere and O. Gorochov, MOCVD growth and characterization of ZnS and $Zn_{1-x}Mg_xS$ alloys 220 (2000) 209
Sammelselg, V., see Aarik, J. 220 (2000) 105
Sammelselg, V., see Aarik, J. 220 (2000) 531
Sato, A., see Kubota, N. 220 (2000) 135
Sazaki, G., see Nakajima, K. 220 (2000) 413
Schlachetzki, A., see Chahoud, M. 220 (2000) 471
Schönherr, H.-P., see Gong, Q. 220 (2000) 23
Shanks, R.A., see Li, N. 220 (2000) 592
Shen, D.Z., see Yang, Y. 220 (2000) 286
Shibata, M., Y. Nitta, K. Fujita and M. Ichikawa, Facets formation of pyramidal Si nanocrystals selectively grown on Si(001) windows in ultrathin SiO_2 films 220 (2000) 449
Shimada, K., see Tsuchiya, T. 220 (2000) 185
Skowronski, M., see Ha, S. 220 (2000) 308
Smilgies, D.-M., N. Boudet, B. Struth, Y. Yamada and H. Yanagi, Highly oriented POPOP films grown on the KCl(001) surface 220 (2000) 88
Solan, A., see Gelfgat, A.Yu. 220 (2000) 316
Song, Z., see Fu, X. 220 (2000) 82
SpringThorpe, A.J., see Najda, S.P. 220 (2000) 226
Stepantsov, E.A., see Roddatis, V.V. 220 (2000) 515
Streater, R.W., see Najda, S.P. 220 (2000) 226
Struth, B., see Smilgies, D.-M. 220 (2000) 88
Stutzmann, M., see Lima, A.P. 220 (2000) 341
Su, Y.K., see Subba Ramaiah, K. 220 (2000) 405
Subba Ramaiah, K., Y.K. Su, S.J. Chang, F.S. Juang and C.H. Chen, Photoluminescence characteristics of Mg- and Si-doped GaN thin films grown by MOCVD technique 220 (2000) 405
Suib, S.L., see Warzywoda, J. 220 (2000) 150
Sun, B.-Q., see Liu, F.-Q. 220 (2000) 439
Sun, C., see Chen, M. 220 (2000) 254
Sun, D.Z., see Gao, F. 220 (2000) 461
Sun, J.L., see Meng, X.J. 220 (2000) 100
Sun, Lianke, see Wang, Changqing 220 (2000) 114

Tabe, Y., S. Hirai and K. Okazaki, Massive CO_2 clathrate hydrate growth at a high-polar-energy surface 220 (2000) 180
Tamura, M., see Wang, D. 220 (2000) 204
Tang, Y.H., see Lam, C. 220 (2000) 466
Tatarchenko, E.V., see Tatarchenko, V.A. 220 (2000) 301
Tatarchenko, V.A., V.S. Uspenski, E.V. Tatarchenko and B. Roux, Theoretical investigation of crystal growth shaping process with the wetting boundary condition 220 (2000) 301
Tateno, K. and C. Amano, Zn-doped AlInAs grown at high temperature by metalorganic chemical vapor deposition 220 (2000) 393

Terashima, K., see Majima, T. 220 (2000) 336

Tomm, Y., P. Reiche, D. Klimm and T. Fukuda, Czochralski grown Ga_2O_3 crystals 220 (2000) 510

Tseng, W.-H., see Wuu, D.-S. 220 (2000) 235

Tsuchiya, T., O. Miki, K. Shimada, M. Ohnishi, A. Wakahara and A. Yoshida, Epitaxial growth of InN films on $MgAl_2O_4$ (1 1 1) substrates 220 (2000) 185

Tsuchiya, T., M. Ohnishi, A. Wakahara and A. Yoshida, Initial stages of InN thin film growth onto $MgAl_2O_4$(1 1 1) and α-Al_2O_3(00·1) substrates 220 (2000) 191

Tu, C.Y., see Lan, C.W. 220 (2000) 619

Turjanska, L., see Höschl, P. 220 (2000) 444

Ujihara, T., see Nakajima, K. 220 (2000) 413

Umeno, A., G. Bacchin and T. Nishinaga, AFM analysis of sidewall formation in low angle incidence microchannel epitaxy of GaAs 220 (2000) 355

Uspenski, V.S., see Tatarchenko, V.A. 220 (2000) 301

Uustare, T., see Aarik, J. 220 (2000) 105

Valcheva-Traykova, M., see Warzywoda, J. 220 (2000) 150

Velázquez, M., C. Haut, B. Hennion and A. Revcolevschi, Crystal growth and characterization of the CMR compound $La_{1.2}(Sr,Ca)_{1.8}Mn_2O_7$ 220 (2000) 480

Videcoq, A., see Vladimirova, M. 220 (2000) 631

Vladimirova, M., A. Pimpinelli and A. Videcoq, A new model of morphological instabilities during epitaxial growth: from step bunching to mounds formation 220 (2000) 631

Wakahara, A., see Tsuchiya, T. 220 (2000) 185

Wakahara, A., see Tsuchiya, T. 220 (2000) 191

Wan, L., X.F. Duan, H. Chen, H. Liu, Z. Li, Q. Huang and J.M. Zhou, Transmission electron microscopy study of hexagonal GaN film grown on GaAs (0 0 1) substrate by using AlAs nucleation layer 220 (2000) 379

Wang, Changqing, Huaijin Zhang, Xianlin Meng, Li Zhu, Y.T. Chow, Xuesong Liu, Ruiping Cheng, Zhaohe Yang, Shaojun Zhang and Lianke Sun, Thermal, spectroscopic properties and laser performance at 1.06 and 1.33 μm of Nd: $Ca_4YO(BO_3)_3$ and Nd:$Ca_4GdO(BO_3)_3$ crystals 220 (2000) 114

Wang, D., Y. Hiroyama, M. Tamura, M. Ichikawa and S. Yoshida, Initial growth of cubic GaN on Si(0 0 1) coated with a thin flat SiC buffer layer 220 (2000) 204

Wang, D.W., see Zhan, J.H. 220 (2000) 231

Wang, H., Y. Zhu and P.P. Ong, Rotary target method to prepare thin films of CdS/SiO_2 by pulsed laser deposition 220 (2000) 554

Wang, J., see Yan, X. 220 (2000) 543

Wang, S., S. Xie, Q. Pang, H. Zheng, Y. Xia, R. Ji, Y. Wu, L. He, Z. Zhu, G. Li and Z. Wang, Temperature quenching mechanisms for photoluminescence of MBE-grown chlorine-doped ZnSe epilayers 220 (2000) 548

Wang, X., see Chen, M. 220 (2000) 254

Wang, X.D., Z.C. Niu, S.L. Feng and Z.H. Miao, 1.35 μm photoluminescence from $In_{0.5}Ga_{0.5}As/GaAs$ islands grown by molecular beam epitaxy via cycled $(InAs)_1/(GaAs)_1$ monolayer deposition 220 (2000) 16

Wang, X.D., see Liu, H.Y. 220 (2000) 216

Wang, X.S., see Yin, J. 220 (2000) 281

Wang, Y.W., see Liang, C.H. 220 (2000) 296

Wang, Z., see Wang, S. 220 (2000) 548

Wang, Z.-G., see Liu, F.-Q. 220 (2000) 439

Wang, Z.G., see Liu, B.L. 220 (2000) 51

Wang, Z.G., see Liu, H.Y. 220 (2000) 216

Warzywoda, J., N. Baç, J.C. Jansen and A. Sacco Jr., Growth of zeolites A and X in low earth orbit 220 (2000) 140

Warzywoda, J., M. Valcheva-Traykova, G.A. Rossetti Jr., N. Baç, R. Joesten, S.L. Suib and A. Sacco Jr., Characterization of zeolites A and X grown in low earth orbit 220 (2000) 150

Wehmann, H.-H., see Chahoud, M. 220 (2000) 471

Wei, Y.Q., see Liu, H.Y. 220 (2000) 216

Wen, L.S., see Chen, M. 220 (2000) 254

Wenzel, A., see Lima, A.P. 220 (2000) 341

Whang, C.N., see Cho, M.-H. 220 (2000) 501

Wichert, D., see Prokofiev, A.V. 220 (2000) 345

Wu, X., see Yan, X. 220 (2000) 543

Wu, Y., see Wang, S. 220 (2000) 548

Wuu, D.-S., R.-H. Horng, W.-H. Tseng, W.-T. Lin and C.-Y. Kung, Influences of temperature ramping rate on GaN buffer layers and subsequent GaN overlayers grown by metalorganic chemical vapor deposition 220 (2000) 235

Xia, Y., see Wang, S. 220 (2000) 548

Xie, S., see Wang, S. 220 (2000) 548

Xie, Y., see Zhan, J.H. 220 (2000) 231

Xu, B., see Liu, H.Y. 220 (2000) 216

Xu, B., see Liu, F.-Q. 220 (2000) 439

Xu, C., see Li, Aidong 220 (2000) 291

Xu, W., Preparing (1 1 1)-oriented C_{60} crystalline films on NaCl substrate 220 (2000) 96

Xu, Z.Y., see Liu, B.L. 220 (2000) 51

Yamada, Y., see Smilgies, D.-M. 220 (2000) 88

Yamamoto, H., see Majima, T. 220 (2000) 336

Yan, X., X. Wu, J. Zhou, Z. Zhang and J. Wang, Growth of laser single-crystals Er:YVO_4 by floating zone method 220 (2000) 543
Yanagi, H., see Smilgies, D.-M. 220 (2000) 88
Yang, G.M., see Cho, H.K. 220 (2000) 197
Yang, M.J., see Bracker, A.S. 220 (2000) 384
Yang, X.G., see Zhan, J.H. 220 (2000) 231
Yang, Y., D.Z. Shen, J.Y. Zhang, X.W. Fan, Z.H. Zhen, X.W. Zhao, D.X. Zhao and Y.N. Liu, The formation process of self-assembled CdSe quantum dots below critical thickness 220 (2000) 286
Yang, Zhaohe, see Wang, Changqing 220 (2000) 114
Ye, H.J., see Meng, X.J. 220 (2000) 100
Yin, J., Z.G. Liu, H. Liu, X.S. Wang, T. Zhu and J.M. Liu, The epitaxial growth of wurtzite ZnO films on $LiNbO_3$ (0001) substrates 220 (2000) 281
Yokota, M., see Kubota, N. 220 (2000) 135
Yoshida, A., see Tsuchiya, T. 220 (2000) 185
Yoshida, A., see Tsuchiya, T. 220 (2000) 191
Yoshida, S., see Wang, D. 220 (2000) 204

Zeng, W., Relaxation mechanism of GaP/InGaAlP/GaAs heterostructure 220 (2000) 538
Zeng, Y.P., see Gao, F. 220 (2000) 457
Zhan, J.H., X.G. Yang, S.D. Li, D.W. Wang, Y. Xie and Y.T. Qian, A chemical solution transport mechanism for one-dimensional growth of CdS nanowires 220 (2000) 231
Zhang, Huaijin, see Wang, Changqing 220 (2000) 114
Zhang, J.Y., see Yang, Y. 220 (2000) 286
Zhang, L.D., see Liang, C.H. 220 (2000) 296
Zhang, M.H., see Zhang, Y.H. 220 (2000) 351
Zhang, Q.-S., see Liu, F.-Q. 220 (2000) 439
Zhang, Shaojun, see Wang, Changqing 220 (2000) 114
Zhang, Y.-Z., see Liu, F.-Q. 220 (2000) 439
Zhang, Y.F., see Lam, C. 220 (2000) 466
Zhang, Y.H., L.W. Lu, M.H. Zhang, Q. Huang, C.L. Bao and J.M. Zhou, Investigation of defects in low-temperature-grown GaAs using optical transient spectroscopy 220 (2000) 351
Zhang, Z., see Yan, X. 220 (2000) 543
Zhao, D.X., see Yang, Y. 220 (2000) 286
Zhao, X.W., see Yang, Y. 220 (2000) 286
Zhen, Z.H., see Yang, Y. 220 (2000) 286
Zheng, H., see Wang, S. 220 (2000) 548
Zhou, G., see Ji, W. 220 (2000) 560
Zhou, J., see Yan, X. 220 (2000) 543
Zhou, J.M., see Zhang, Y.H. 220 (2000) 351
Zhou, J.M., see Wan, L. 220 (2000) 379
Zhu, Li, see Wang, Changqing 220 (2000) 114
Zhu, T., see Yin, J. 220 (2000) 281
Zhu, Y., see Wang, H. 220 (2000) 554
Zhu, Z., see Wang, S. 220 (2000) 548

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Journal of Crystal Growth 220 (2000) 644–645

JOURNAL OF CRYSTAL GROWTH

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Subject index

Apparatus
- for the growth of shaped gallium antimonide crystals 1
- for the growth of silicon carbide 308
- for silicon nano particles 466

Computer simulation
- of annealed gallium arsenide 6
- of binding energy 254
- of macromolecular crystal growth 130
- of sublimation 243
Constitutional supercooling
- of indium gallium antimonide 39
Convection 75, 166, 316, 326, 619

Device characterization
- electronic materials 75, 82, 351, 405
- heterojunction 16, 46, 220, 457, 538
- lasers 197, 439
- quantum wells 439
- quantum wires and dots 16, 51, 216, 432
Diffusional control
- of ammonium chloride 326
- of beryllium 46
- of directional adatoms 364
- of titanium carbide 296
Diodes, see Device characterization

Electronic materials, see Device characterization
Epitaxy, see Thin film growth
Etching
- chemical 39, 56, 522

Heat flow control
- of annealed gallium arsenide 6
- of Bridgman method 619
- of macromolecular crystal growth 130
Heterojunctions, see Device characterization
Hydrodynamics, see Convection

Kinetics
- of growth 75, 135, 161, 296, 449, 461, 471, 610, 631
- of interface control 100, 180
- of nucleation 296, 531
- of self assembled quantum dots 286

Lasers, see Device characterization
Lasers, crystals for
- calcium gadolinium oxoborate 114
- calcium lithium niobium gallium garnet 121
- calcium yttrium oxoborate 114
- yttrium vanadate 543

Melt growth technique
- by Czochralski method
- - of aluminum tungstate 176
- - of calcium gadolinium oxoborate 114
- - of calcium yttrium oxoborate 114
- - of indium gallium antimonide 39
- - of gallium oxide 510
- - of lanthanum gallium oxide 275
- - theory of shaped growth 301
- by edged defined film fed growth
- - of shaped gallium antimonide crystals 1
- by floating zone method
- - of lanthanum manganese oxide 480
- - of yttrium vanadate 543
Microgravity, growth under
- of zeolite 140, 150
Morphological stability
- of cupler 592
- of growing surface 631

Nucleation
- of calcium sulfate dihydrate 579
- of gibbsite 572
- of nickel silicon 488
- of zeolite 140, 150
Numbers
- Grashof 166
- Peclet 166
- Rayleigh 326, 619
- Schmidt 166

Phase diagram
- of III–V surface reconstruction 384
- of cadmium telluride 444
- of carbon tetrachloride 161
- of indium gallium arsenide system 413
- of lead magnesium strontium sulfate 126

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Quantum structures, see Device characterization
Quantum wells, see Device characterization
Quantum wires and dots, see Device characterization

Solid growth technique
- by arc discharge
- - of gallium oxide 494
- by sol gel
- - of lanthanum nickel oxide 100
- - of lead zirconate titanate 82
- by solid phase intergrowth
- - of zirconia 515
- - of zinc oxide 515
Solution growth technique
- by flux
- - of lithium cupric vanadate 345
- by hydrothermal 140, 150
- by top seeded solution
- - of mixed niobate borate 263
- - theory of chemical solution transport 231
- by low temperature method
- - of gallium arsenide 351
- - of L-arginine phosphate monohydrate 291
Superconductivity materials, high Tc
- - of BSCCO 68
Surface energy, determination
- of high polar energy surface 180
Surface structure
- of 1,4-bis(5-phenyloxazol-2-yl)benzene 88
- of aluminum gallium arsenide antimonide
- of macromolecular crystal growth 130

Thin film growth, epitaxy
- by atomic layer epitaxy
- - of hafnium dioxide 105
- - of gallium arsenide 351
- - of titanium dioxide 531
- by liquid phase epitaxy
- - of indium gallium arsenide 413
- - of silicon carbide 75
- by metalorganic molecular beam epitaxy
- - of aluminum gallium indium phosphide 226
- by molecular beam epitaxy
- - of 1,4-bis(5-phenyloxazol-2-yl)benzene 88
- - of aluminum gallium nitride 432
- - of aluminum gallium indium nitride 341
- - of aluminum antimonide 384
- - of bismuth strontium calcium cuprate 68
- - of gallium arsenide 23, 355
- - of gallium antimonide 384
- - of gallium nitride 204, 341, 379, 432
- - of indium arsenide 16, 216, 384
- - of indium aluminum arsenide 51, 216
- - of indium gallium arsenide 16
- - of indium gallium nitride 401
- - of silicon 457
- - of silicon carbide 204
- - of silicon germanium 457
- - of zinc selenide 548
- by gas source molecular beam epitaxy
- - of indium gallium arsenide 46
- - of indium phosphide 46
- by pulsed laser deposition
- - of cadmium sulfide 554
- by vapor phase epitaxy
- - through chemical vapor deposition
- - - of gallium aluminum arsenide 56
- - - of lithium niobate tantalate 336
- - - of silicon 461
- - - of silicon dioxide 449
- - - of silicon carbide 560
- - - theory of simultaneous etching and growth 98
- - through ion beam
- - - of yttria 501
- - through metalorganic chemical vapor deposition
- - - of aluminum indium arsenide 393
- - - of aluminum gallium nitride 62
- - - of cadmium selenide 286
- - - of gallium arsenide 364, 425, 538
- - - of gallium phosphide 538
- - - of gallium nitride 235, 405
- - - of indium arsenide 425
- - - of indium gallium aluminum phosphide 538
- - - of indium phosphide 471
- - - of indium gallium arsenide
- - - of indium gallium nitride 197
- - - of indium nitride 185, 191
- - - of tantalum nitride 604
- - - of zinc sulfide 209
- - - of zinc magnesium sulfide 209
- - through pulsed laser deposition
- - - of zinc oxide 281

Vapor growth technique
- by evaporation and condensation
- - of cadmium telluride 30
- - of fulleren single crystals 96
- by sublimation
- - of aluminum nitride 243